

General Description

The AGM60P85E combines advanced trench MOSFET technology with a low resistance package to provide extremely low $R_{DS(ON)}$.

This device is ideal for load switch and battery protection applications.

Features

- Advance high cell density Trench technology
- Low $R_{DS(ON)}$ to minimize conductive loss
- Low Gate Charge for fast switching
- Low Thermal resistance

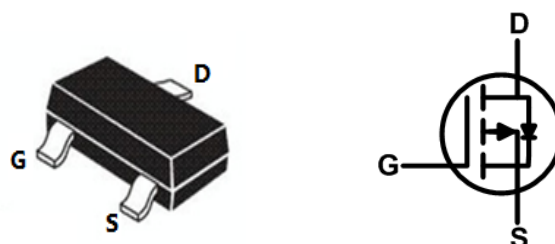
Application

- MB/VGA Vcore
- SMPS 2nd Synchronous Rectifier
- POL application
- BLDC Motor driver

Product Summary

BVDSS	RDSON	ID
-60V	115mΩ	-3A

SOT-23-3 Pin Configuration



Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
60P85	AGM60P85E	SOT-23-3	----	----	3000

Table 1. Absolute Maximum Ratings (TA=25°C)

Symbol	Parameter	Value	Unit
VDS	Drain-Source Voltage (VGS=0V)	-60	V
VGS	Gate-Source Voltage (VDS=0V)	±20	V
ID	Drain Current-Continuous(Tc=25°C) (Note 1)	-3.0	A
	Drain Current-Continuous(Tc=100°C)	-1.2	A
IDM (pulse)	Drain Current-Continuous@ Current-Pulsed (Note 2)	-12	A
PD	Maximum Power Dissipation(Tc=25°C)	2.5	w
	Maximum Power Dissipation(Tc=100°C)	1.0	w
EAS	Avalanche energy (Note 3)	--	mJ
TJ,TSTG	Operating Junction and Storage Temperature Range	-55 To 150	°C

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
RθJA	Thermal Resistance Junction-ambient (Steady State) ¹	---	85	°C/W
RθJC	Thermal Resistance Junction-Case ¹	---	50	°C/W

Table 3. Electrical Characteristics (TA=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BVDSS	Drain-Source Breakdown Voltage	VGS=0V ID=250μA	-60	--	--	V
IDSS	Zero Gate Voltage Drain Current	VDS=-60V,VGS=0V	--	--	-1	μA
IGSS	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	nA
VGS(th)	Gate Threshold Voltage	VDS=VGS,ID=-250μA	-1.0	--	-2.5	V
gFS	Forward Transconductance	VDS=-5V,ID=-3A	--	5.8	--	S
RDS(on)	Drain-Source On-State Resistance	VGS=-10V, ID=-3A	--	115	140	mΩ
		VGS=-4.5V, ID=-2A	--	165	190	mΩ
Dynamic Characteristics						
Ciss	Input Capacitance	VDS=-15V,VGS=0V, F=1MHZ	--	715	--	pF
Coss	Output Capacitance		--	51	--	pF
Crss	Reverse Transfer Capacitance		--	34	--	pF
Rg	Gate resistance	VGS=0V, VDS=0V,f=1.0MHz	--	--	--	Ω
Switching Times						
td(on)	Turn-on Delay Time	VGS=-10V,VDS=-12V, ID=-3A,RGEN=3.3Ω	--	10	--	nS
tr	Turn-on Rise Time		--	17	--	nS
td(off)	Turn-Off Delay Time		--	22	--	nS
tf	Turn-Off Fall Time		--	21	--	nS
Qg	Total Gate Charge	VGS=-4.5V, VDS=-20V, ID=-3A	--	5.9	--	nC
Qgs	Gate-Source Charge		--	2.9	--	nC
Qgd	Gate-Drain Charge		--	1.8	--	nC
Source-Drain Diode Characteristics						
ISD	Source-Drain Current(Body Diode)		--	--	-3.0	A
VSD	Forward on Voltage	VGS=0V,IS=-1A	--	--	-1.2	V
trr	Reverse Recovery Time	IF=-1A , dl/dt=100A/μs , TJ=25℃	--	--	--	ns
Qrr	Reverse Recovery Charge		--	--	--	nc

Notes 1.The maximum current rating is package limited.

Notes 2.Repetitive Rating: Pulse width limited by maximum junction temperature

Notes 3.EAS condition: TJ=25°C

P-Channel Typical Characteristics

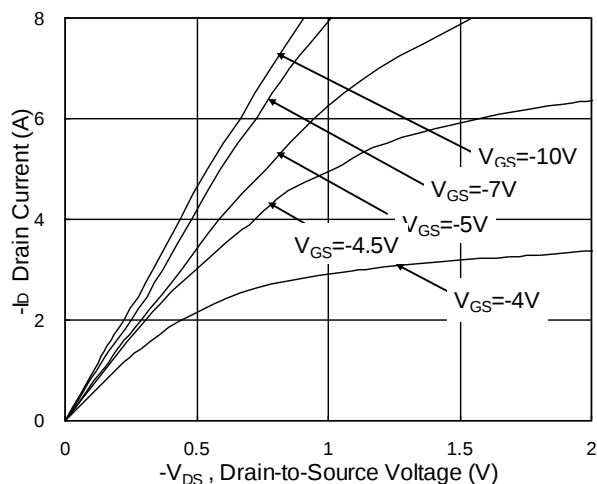


Fig.1 Typical Output Characteristics

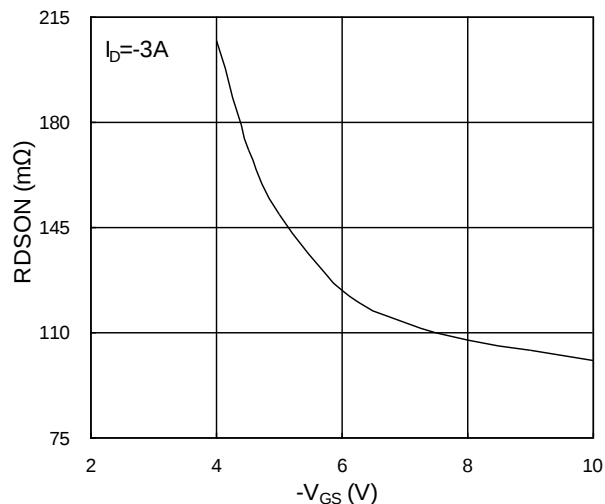


Fig.2 On-Resistance vs. G-S Voltage

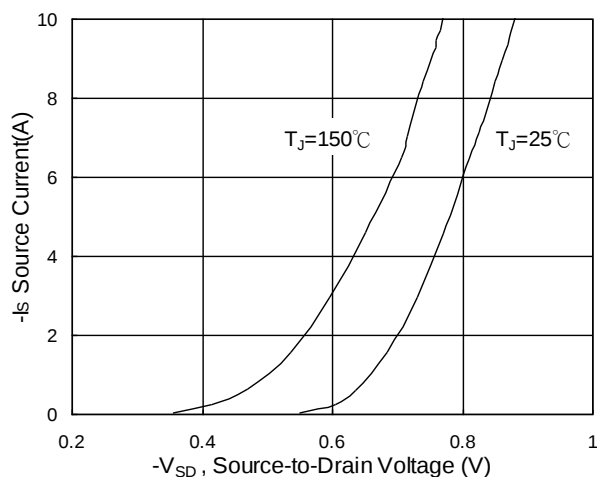


Fig.3 Forward Characteristics Of Reverse

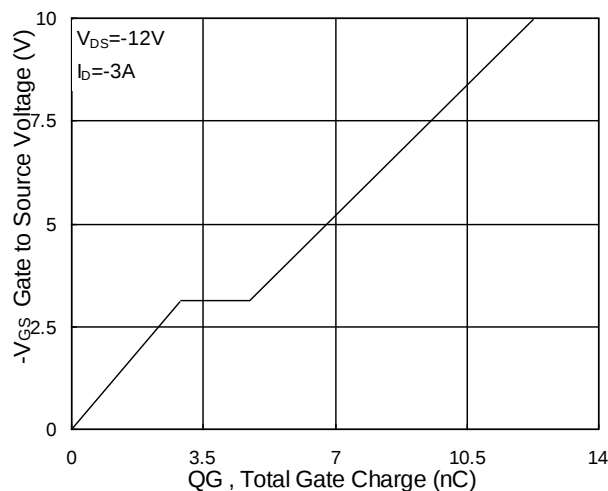


Fig.4 Gate-Charge Characteristics

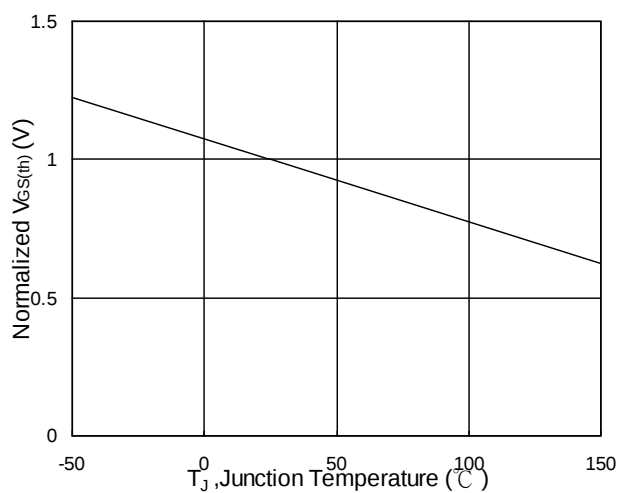


Fig.5 Normalized $V_{GS(th)}$ vs. T_J

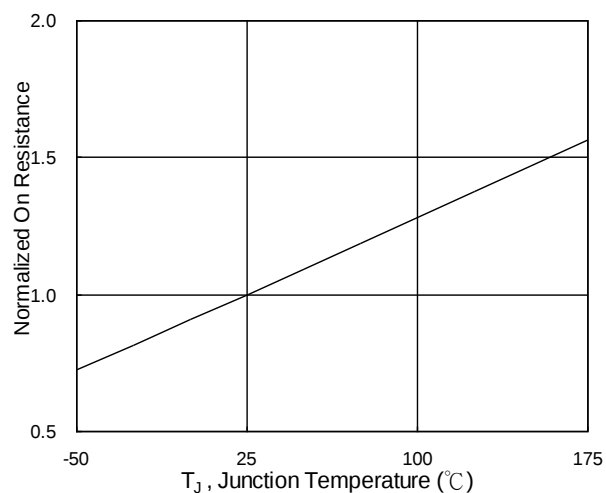


Fig.6 Normalized $R_{DS(on)}$ vs. T_J

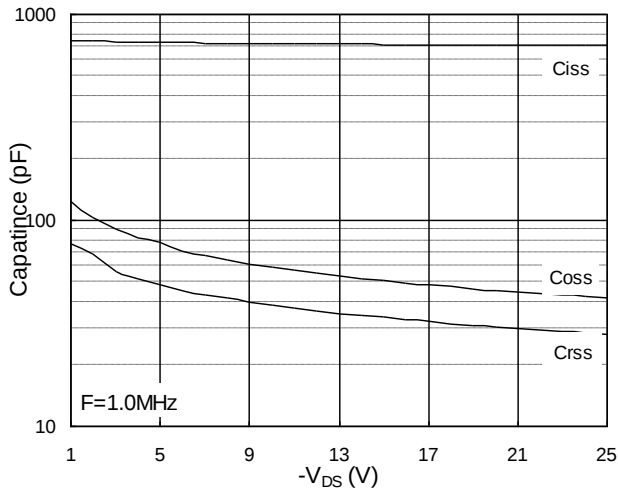


Fig.7 Capacitance

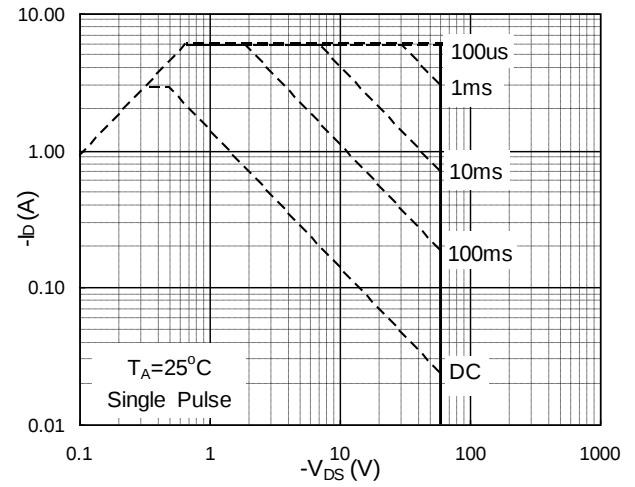


Fig.8 Safe Operating Area

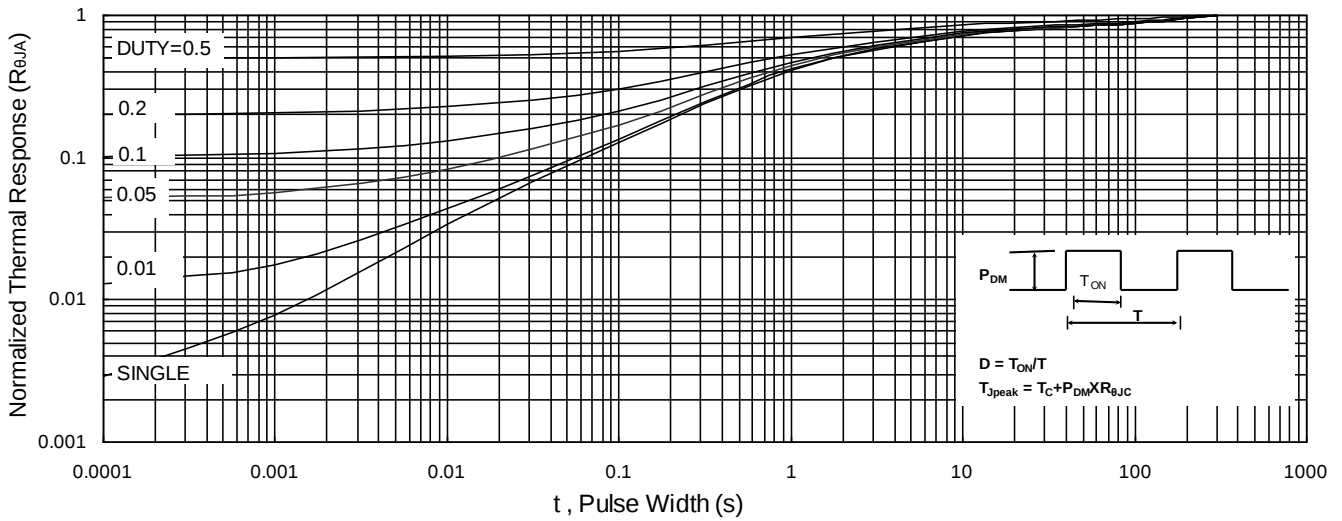


Fig.9 Normalized Maximum Transient Thermal Impedance

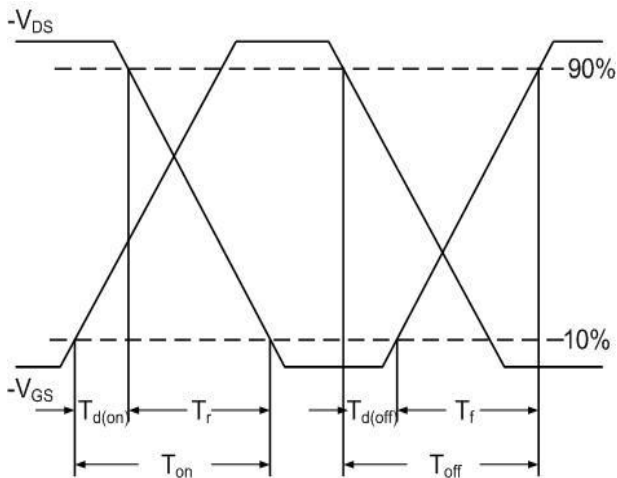


Fig.10 Switching Time Waveform

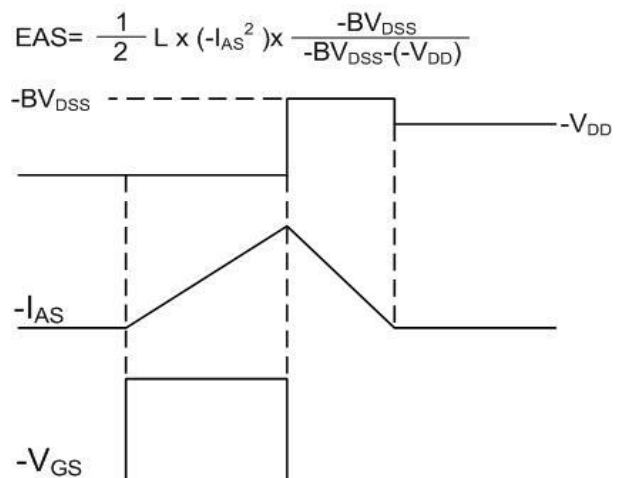
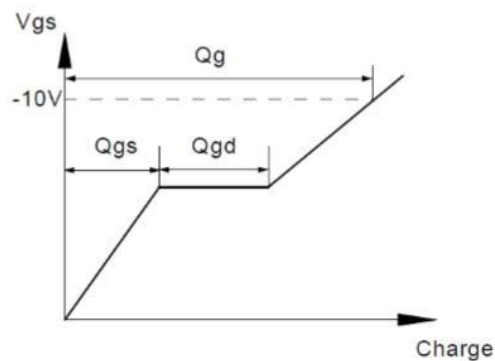
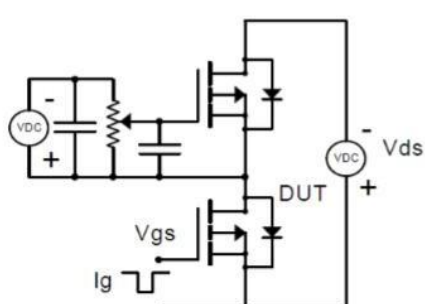


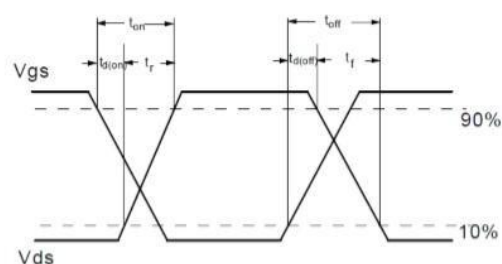
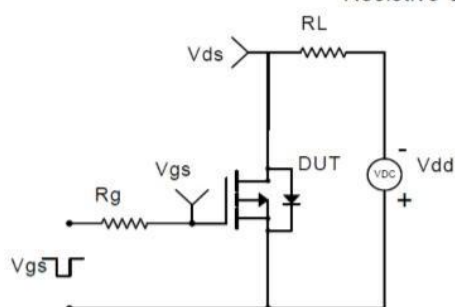
Fig.11 Unclamped Inductive Waveform

Test Circuit

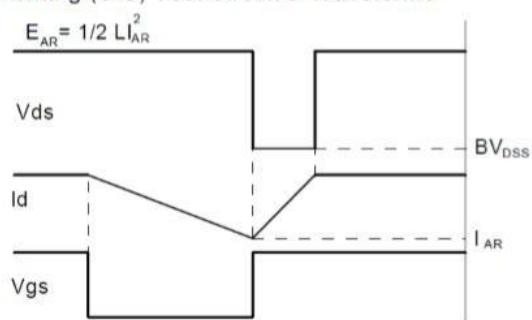
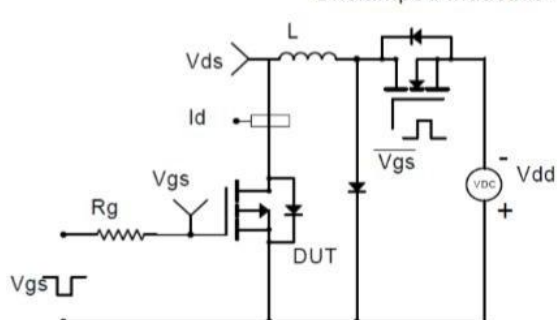
Gate Charge Test Circuit & Waveform



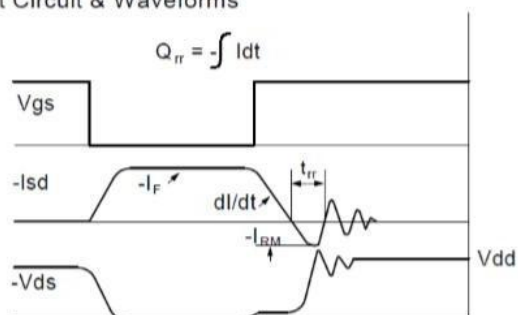
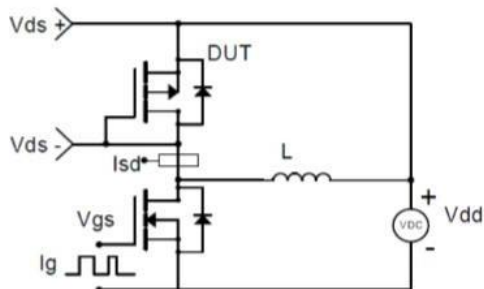
Resistive Switching Test Circuit & Waveforms



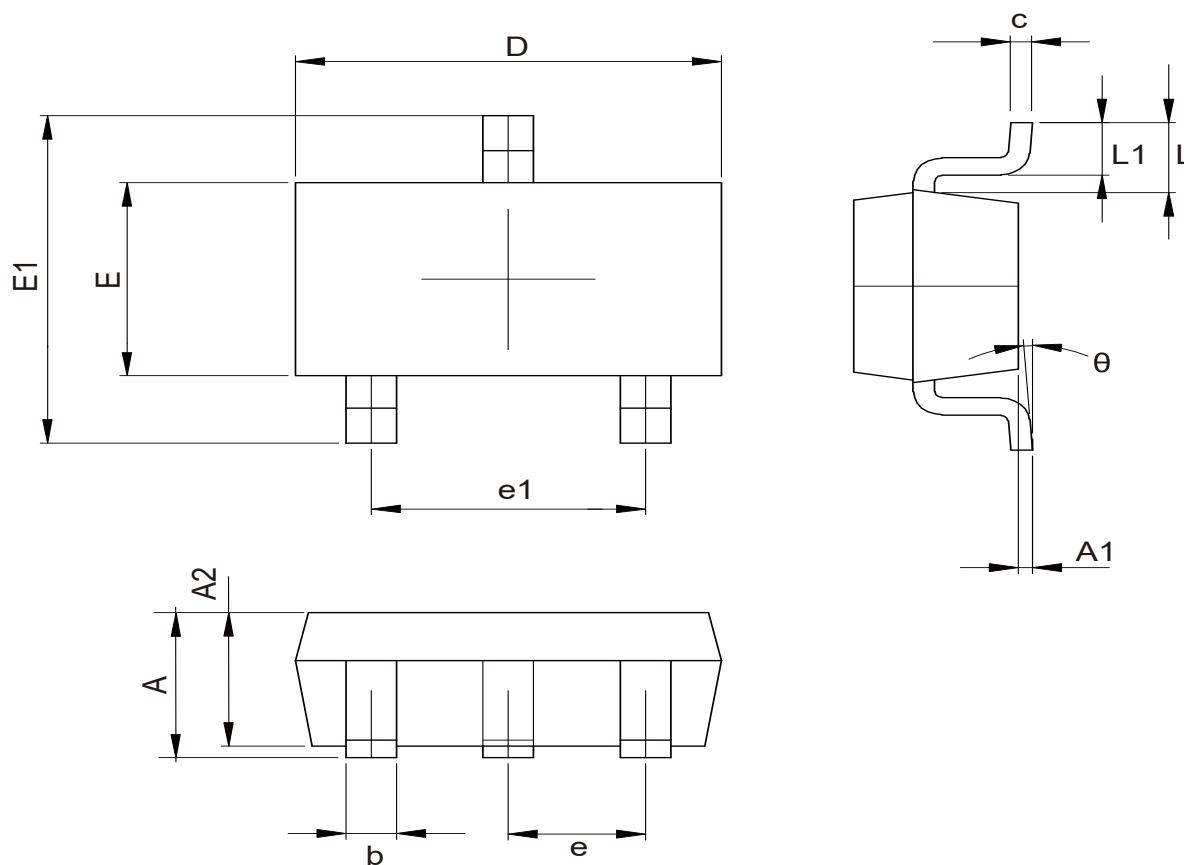
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



SOT-23-3L
PACKAGE OUTLINE DIMENSIONS



COMMON DIMENSIONS CUNITS MEASURE=MILLIMETER			
SYMBOL	MIN	NOM	MAX
A	1.050	—	1.300
A1	0.000	—	0.200
A2	1.050	—	1.200
b	0.300	0.400	0.500
c	0.100	—	0.200
D	2.820	2.900	3.020
E	1.500	1.600	1.700
E1	2.650	2.800	2.950
e	0.950TYP		
e1	1.800	1.900	2.000
L	0.6REF		
L1	0.300	0.450	0.600
θ	0°	—	8°

Unit:mm

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